

a cell plate electrode including a tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film, wherein the tantalum nitride films of said storage electrode and said cell plate electrode each have a work function greater than 4.95eV.

2. (Three Times Amended) A semiconductor device, comprising:

a storage electrode including a first tantalum nitride film formed over a semiconductor substrate;

a capacitor dielectric film including a tantalum oxide film formed on and contacting an upper surface of said first tantalum nitride film; and

a cell plate electrode including a second tantalum nitride film formed on and contacting an upper surface of said tantalum oxide film and a copper film formed on and contacting an upper surface of said second tantalum nitride film, wherein said first and second tantalum nitride films each have a work function greater than 4.95eV.

Please add the following:

--7. (New) The semiconductor device according to claim 1, wherein said work function of the tantalum nitride films is up to 5.41eV.

8. (New) The semiconductor device according to claim 1, wherein said work function of the tantalum nitride films is equal to or greater than 5.41eV.